

2525 Shader Road, Orlando Florida 32804 USA Phone: 407-298-2000 Fax: 407-293-2979 Website: mtronpti.com NYSE MKT: LGL



Specification for a 4-Pole 5x7mm SMD Monolithic Crystal Filter MtronPTI P/N: XF9402R

I. General & Electrical Requirements

- 1. Center Frequency (F_O): 21.4MHz
- 2. Passband @ 3dB: F_O ±9.0kHz minimum
- 3. Insertion Loss (@F₀): 4.0dB maximum
- 4. Passband Ripple (peak-valley): 1.0dB maximum
- 5. Group Delay Variation:

Over $F_0 \pm 7.5$ kHz: $\leq 25 \mu sec$

Over $F_0 \pm 9.0 \text{kHz}$: $\leq 35 \ \mu sec$

6. Attenuation (minimum relative to IL at F₀):

20dB: F_O ±24.0kHz maximum

40dB: F_O ±49.0kHz maximum

60dB: $F_0 \pm 125.00$ kHz maximum

- 7. Ultimate Attenuation: 60dB minimum, F₀-910kHz
- 8. Spurious Response: 17dB minimum
- 9. Coupling Capacitance (C_C): 2.5pF
- 10. Input Signal Level: ≤ 0dBm
- 11. Insulation Resistance (100 V_{DC}): > 500 $M\Omega$
- 12. Z_S/Z_L : 2800 Ω // 0.7pF typical

MtronPTI MODEL: XF9402R

ENG APPROVAL:

DATE:

MFG APPROVAL

10/12/13

Note 1: All electrical performance specifications are to be met over the -40 $^{\circ}$ C to +85 $^{\circ}$ C Operating Temperature Range.

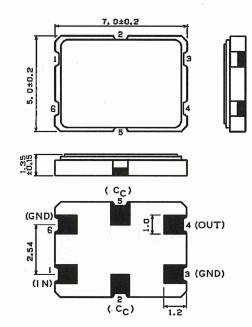
II. Environmental, Test & Physical Requirements:

1. Temperature Range:

Operating: -40°C to +85°C

Storage: -55°C to +105°C

- 2. Solderability: Peak Reflow Temperature +240°C ±5°C
- 3. Humidity: $95\% \pm 3\%$ @ ± 40 °C for 96-hours
- 4. Seal: Hermetic
- 5. Shock (survival): RTCA DO-160F Section 8, Category B
- Vibration (survival): RTCA DO-160F Section 7, Category S Test Curves C, B3, L & M. Category U Test Curve G
- 7. Temperature Cycle: -40°C 30-minutes/cycle; +85°C 30-minutes/cycle
- 8. Package: Single 5x7mm (ref drawing)
- 9. RoHS: Full RoHS Compliance



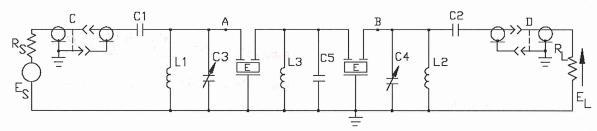


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III. 50Ω Matching Network:



RS = RL = 50 DHMS

 $C1 = \frac{19.5}{PARALLEL}$ pF NOM. (SELECT FOR CORRECT SOURCE PARALLEL RESISTANCE.)

C2 = $\underline{19.5}$ pF NOM. (SELECT FOR CORRECT LOAD PARALLEL RESISTANCE.)

C3 = C4 = 0.8 - 10 pF (TRIMMER)

L1 = L2 = 29T #28 AWG ON T25-6 CORE

L3 = SELECT AT TEST FIXTURE BUILD TO ENSURE CORRECT Z_C .

Z SOURCE = 2800 // +0.7PF

 $Z L \Box AD = 2800 // +0.7 PF$

 $Z_C = C5 = 2.5PF$

Z SOURCE AND Z LOAD ARE THE IMPEDANCES AT POINTS A AND B, RESPECTIVELY, WITH THE FILTER REMOVED AND THE TEST FIXTURE TERMINATED WITH A 50 DHM RESISTIVE LOAD.

NOTES: 1.> C3 AND C4 ARE ADJUSTED FOR (CHECK ONE):

X OPTIMUM PASSBAND CHARACTERISTIC
SPECIFIED SOURCE AND LOAD REACTANCE OF
C5 ADJUSTED FOR (CHECK DNE)

X OPTIMUM PASSBAND CHARACTERISTIC
FIXED JUNCTION CAPACITANCE OF

2.) FLAT LOSS IS THE RATIO OF POWER DELIVERED TO THE LOAD, TO THE AVAILABLE POWER, EXPRESSED IN dB.

A, EXCLUDING TEST FIXTURE LOSS (EQUAL SOURCE & LOAD RESISTANCE): FLAT LOSS = 20 LOG $_{10}$ (E $_{\rm L1}/{\rm E}_{\rm L2}$)

 E_{L1} = EL WITH FILTER REPLACED BY A SHORT FROM A TO B & C_3 , C_4 TUNED FOR MAX EL AT FON.

E_{L2} = E_L WITH FILTER INSTALLED, C₃ & C₄
TUNED PER NOTE 1, AND FREQUENCY
PER NOTE 2.

B. INCLUDING TEST FIXTURE LOSS
FLAT LOSS = 20 LOG10 (EL3/EL2)
EL3 = EL WITH TEST FIXTURE REMOVED & C
CONNECTED TO D.

3.) INITIAL LEVEL OF E SUCH THAT E $_{13}$ = 0.224 VOLTS $_{\pm 10\%}$ (SOURCE POWER = 0 $_{\pm 1}$ dBm.) E $_{5}$ HELD CONSTANT DURING ALL MEASUREMENT.

IV. Datasheet Revision Table:

Date	Rev.	Orig.	Details of Revision
10/16/13	Е	BRM	Updated with 50Ω matching network diagram.